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(12) United States Patent Lin et al.

(54) PROTECTIVE COVER FOR AN ACOUSTIC WAVE DEVICE AND FABRICATION METHOD THEREOF

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(57) ABSTRACT

A protective cover for an acoustic wave device and a fabrication method thereof, for protecting an acoustic wave device having a resonant area during a packaging operation so as to avoid molding compound flowing onto the resonant area of the acoustic wave device. The fabrication method comprises: defining a sacrificial area on the acoustic wave device; forming a sacrificial layer on the sacrificial area; covering a metal covering layer on the sacrificial layer and connecting a bottom rim of the metal covering layer to the acoustic wave device and forming an opening between the bottom rim of the metal covering layer and the acoustic wave device; and removing the sacrificial layer to form a cavity between the metal covering layer and the resonant area by using a chemical solution, wherein the chemical solution enters from the opening between the metal covering layer and the acoustic wave device.

10 Claims, 7 Drawing Sheets

